

L Number	Hits	Search Text	DB	Time stamp
1	5628	tab near3 lead	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:18
2	1951	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:19
3	92	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with (electrode terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:26
4	21	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with ((electrode terminal pad) near3 (chip die ic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:29
-	909	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:17
-	468	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process) and (inject injecting injected)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 09:57
-	403	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 09:58
-	1	((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and ((releasable released releasing) near1 (layer film material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:08
-	101	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:03
-	63	(((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)) and ((flipchip (flip adj chip) bump ball)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:04
-	179	(mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:10
-	12	((mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:27
-	0	6123895.URPN.	USPAT	2002/09/20 10:16
-	5	("3178807"   "5006417"   "5384087"   "5616421"   "5902943").PN.	USPAT	2002/09/20 10:16
-	1	jp408142106a	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:29

-	156	MIYAJIMA-FUMIO	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:30
-	19	MIYAJIMA-FUMIO	USPAT; EPO	2002/09/20 10:30
-	1	6187243.pn. and (parting adj face)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 14:01
-	1481	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:59
-	39173	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:58
-	54	(mold near2 (upper lower)) near3 (air adj vent)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:59
-	8	((mold near2 (upper lower)) near3 (air adj vent)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 14:59